Zibo Seno Electronic Engineering Co., Ltd.



SB3040PT – SB30200PT 🕲



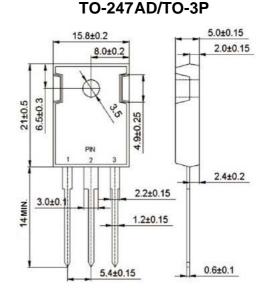
30.0A SCHOTTKY BARRIER DIODE

Features

- Schottky Barrier Chip
- Ideally Suited for Automatic Assembly
- Low Power Loss, High Efficiency
- For Use in Low Voltage Application
- Guard Ring Die Construction
- Plastic Case Material has UL Flammability Classification Rating 94V-O

Mechanical Data

- Case: TO-247AD/TO-3P, Molded Plastic
- Terminals: Plated Leads Solderable per
- MIL-STD-202, Method 208
 Polarity: See Diagram
- Mounting Position: Any
- Lead Free: For RoHS / Lead Free Version



Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

| Characteristic | Symbol | SB 3040 PT | SB 3045 PT | SB 3050 PT | SB 3060 PT | SB 30100 PT | SB 30150 PT | SB 30200 PT | Unit |
|---|--------------------|------------------|------------------|------------------|------------------|-------------------|-------------------|-------------------|------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | Vrrm Vrwm Vr | 40 | 45 | 50 | 60 | 100 | 150 | 200 | V |
| RMS Reverse Voltage | VR(RMS) | 28 | 31 | 35 | 42 | 70 | 105 | 140 | V |
| Average Rectified Output Current $@T_L = 75^{\circ}C$ (Note 1) | lo | 30 | | | | | | | А |
| Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method) | IFSM | 275 | | | | | | A | |
| Forward Voltage $@I_F = 15A$ | Vfm | 0.70 | | 0.75 | | 0.80 | 0.90 | | V |
| Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$ | Iгм | 0.2 20 | | | | | | | mA |
| Typical Junction Capacitance (Note 2) | Cj | 350 | | 2 | 30 | | 200 | | pF |
| Typical Thermal Resistance (Note 1) | R∂JA | 3.0 2.0 | | | | °C/W | | | |
| Operating and Storage Temperature Range | Тj, Tsтg | -55 to +150 | | | | | | | °C |

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

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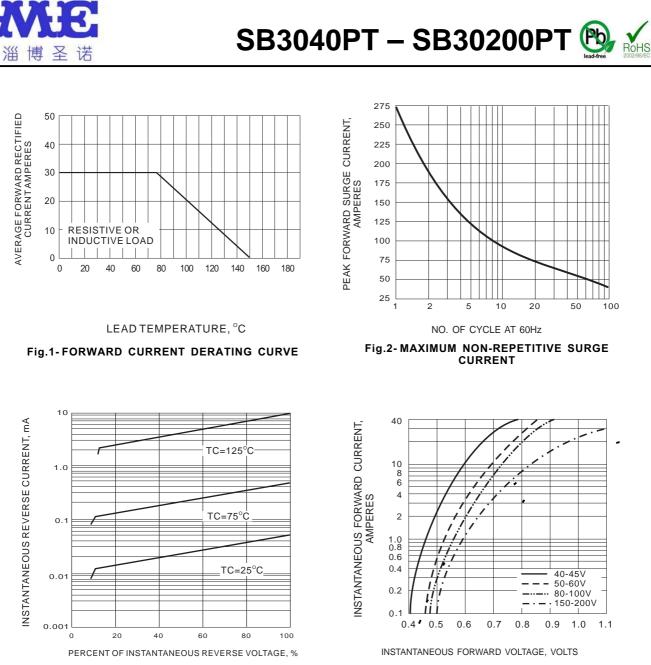


Fig.3- TYPICAL REVERSE CHARACTERISTIC

Fig.4- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTIC